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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	9216
Total RAM Bits	55296
Number of I/O	178
Number of Gates	400000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl400v5-fgg256

field upgrades with confidence that valuable intellectual property cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The IGLOO family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the IGLOO family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/communications, computing, and avionics markets.

Firm-Error Immunity

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of IGLOO flash-based FPGAs. Once it is programmed, the flash cell configuration element of IGLOO FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Advanced Flash Technology

The IGLOO family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

IGLOO family FPGAs utilize design and process techniques to minimize power consumption in all modes of operation.

Advanced Architecture

The proprietary IGLOO architecture provides granularity comparable to standard-cell ASICs. The IGLOO device consists of five distinct and programmable architectural features (Figure 1-1 on page 1-4 and Figure 1-2 on page 1-4):

- Flash*Freeze technology
- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory[†]
- Extensive CCCs and PLLs[†]
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the IGLOO core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC[®] family of third-generation-architecture flash FPGAs.

[†] The AGL015 and AGL030 do not support PLL or SRAM.

Flash*Freeze Technology

The IGLOO device has an ultra-low power static mode, called Flash*Freeze mode, which retains all SRAM and register information and can still quickly return to normal operation. Flash*Freeze technology enables the user to quickly (within 1 μ s) enter and exit Flash*Freeze mode by activating the Flash*Freeze pin while all power supplies are kept at their original values. In addition, I/Os and global I/Os can still be driven and can be toggling without impact on power consumption, clocks can still be driven or can be toggling without impact on power consumption, and the device retains all core registers, SRAM information, and states. I/O states are tristated during Flash*Freeze mode or can be set to a certain state using weak pull-up or pull-down I/O attribute configuration. No power is consumed by the I/O banks, clocks, JTAG pins, or PLL, and the device consumes as little as 5 μ W in this mode.

Flash*Freeze technology allows the user to switch to active mode on demand, thus simplifying the power management of the device.

The Flash*Freeze pin (active low) can be routed internally to the core to allow the user's logic to decide when it is safe to transition to this mode. It is also possible to use the Flash*Freeze pin as a regular I/O if Flash*Freeze mode usage is not planned, which is advantageous because of the inherent low power static (as low as 12 μ W) and dynamic capabilities of the IGLOO device. Refer to Figure 1-3 for an illustration of entering/exiting Flash*Freeze mode.

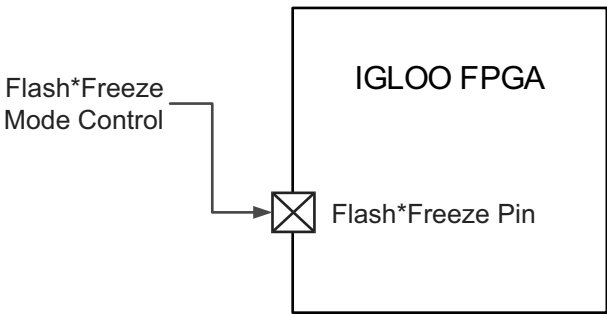


Figure 1-3 • IGLOO Flash*Freeze Mode

VersaTiles

The IGLOO core consists of VersaTiles, which have been enhanced beyond the ProASIC^{PLUS}® core tiles. The IGLOO VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to Figure 1-4 for VersaTile configurations.

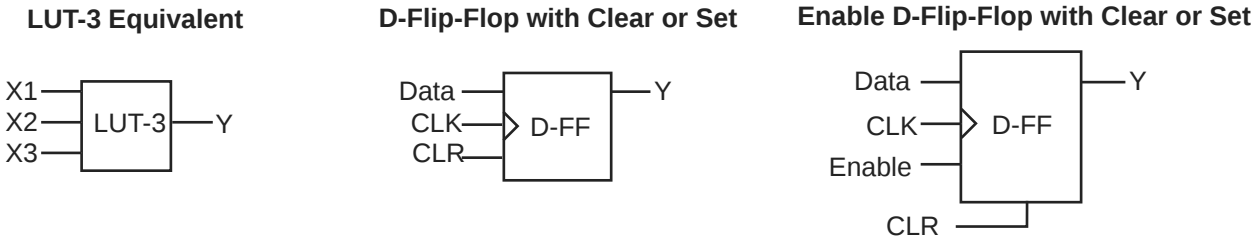


Figure 1-4 • VersaTile Configurations

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz up to 250 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz up to 250 MHz
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% $\pm$ 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% $\times$ clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time is 300 μ s (for PLL only)
- Exceptional tolerance to input period jitter—allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases of 40 ps $\times$ 250 MHz / f_{OUT_CCC} (for PLL only)

Global Clocking

IGLOO devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

I/Os with Advanced I/O Standards

The IGLOO family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.0 V wide range, and 3.3 V). IGLOO FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported (Table 1-1).

Table 1-1 • I/O Standards Supported

I/O Bank Type	Device and Bank Location	I/O Standards Supported		
		LVTTL/ LVCMOS	PCI/PCI-X	LVPECL, LVDS, B-LVDS, M-LVDS
Advanced	East and west banks of AGL250 and larger devices	✓	✓	✓
Standard Plus	North and south banks of AGL250 and larger devices All banks of AGL060 and AGL125K	✓	✓	Not supported
Standard	All banks of AGL015 and AGL030	✓	Not supported	Not supported

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

IGLOO banks for the AGL250 device and above support LVPECL, LVDS, B-LVDS, and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Table 2-2 • Recommended Operating Conditions¹

Symbol	Parameter		Commercial	Industrial	Units
T _J	Junction Temperature ²		0 to +85	–40 to +100	°C
VCC ³	1.5 V DC core supply voltage ⁵		1.425 to 1.575	1.425 to 1.575	V
	1.2 V–1.5 V wide range DC core supply voltage ^{4,6}		1.14 to 1.575	1.14 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode	3.15 to 3.45	3.15 to 3.45	V
		Operation ⁷	0 to 3.6	0 to 3.6	V
VCCPLL ⁸	Analog power supply (PLL)	1.5 V DC core supply voltage ⁵	1.425 to 1.575	1.425 to 1.575	V
		1.2 V – 1.5 V DC core supply voltage ^{4,6}	1.14 to 1.575	1.14 to 1.575	V
VCCI and VMV ⁹	1.2 V DC core supply voltage ⁶		1.14 to 1.26	1.14 to 1.26	V
	1.2 V DC wide range DC supply voltage ⁶		1.14 to 1.575	1.14 to 1.575	V
	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.0 V DC supply voltage ¹⁰		2.7 to 3.6	2.7 to 3.6	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	LVDS differential I/O		2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. All parameters representing voltages are measured with respect to GND unless otherwise specified.
2. Software Default Junction Temperature Range in the Libero SoC software is set to 0°C to +70°C for commercial, and -40°C to +85°C for industrial. To ensure targeted reliability standards are met across the full range of junction temperatures, Microsemi recommends using custom settings for temperature range before running timing and power analysis tools. For more information on custom settings, refer to the New Project Dialog Box in the Libero SoC Online Help.
3. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-25 on page 2-24. VCCI should be at the same voltage within a given I/O bank.
4. All IGLOO devices (V5 and V2) must be programmed with the VCC core voltage at 1.5 V. Applications using the V2 devices powered by 1.2 V supply must switch the core supply to 1.5 V for in-system programming.
5. For IGLOO® V5 devices
6. For IGLOO V2 devices only, operating at VCCI ≥ VCC.
7. VPUMP can be left floating during operation (not programming mode).
8. VCCPLL pins should be tied to VCC pins. See the "Pin Descriptions" chapter of the IGLOO FPGA Fabric User Guide for further information.
9. VMV and VCCI must be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" on page 3-1 for further information.
10. 3.3 V wide range is compliant to the JESD-8B specification and supports 3.0 V VCCI operation.

Combinatorial Cells Contribution— P_{C-CELL}

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

Routing Net Contribution— P_{NET}

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution— P_{INPUTS}

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution— $P_{OUTPUTS}$

$$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-23 on page 2-19.

β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-24 on page 2-19.

F_{CLK} is the global clock signal frequency.

RAM Contribution— P_{MEMORY}

$$P_{MEMORY} = P_{AC11} * N_{BLOCKS} * F_{READ-CLOCK} * \beta_2 + P_{AC12} * N_{BLOCK} * F_{WRITE-CLOCK} * \beta_3$$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{READ-CLOCK}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations.

$F_{WRITE-CLOCK}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in Table 2-24 on page 2-19.

PLL Contribution— P_{PLL}

$$P_{PLL} = P_{DC4} + P_{AC13} * F_{CLKOUT}$$

F_{CLKOUT} is the output clock frequency.[†]

[†] If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($P_{AC13} * F_{CLKOUT}$ product) to the total PLL contribution.

Guidelines

Toggle Rate Definition

A toggle rate defines the frequency of a net or logic element relative to a clock. It is a percentage. If the toggle rate of a net is 100%, this means that this net switches at half the clock frequency. Below are some examples:

- The average toggle rate of a shift register is 100% because all flip-flop outputs toggle at half of the clock frequency.
- The average toggle rate of an 8-bit counter is 25%:
 - Bit 0 (LSB) = 100%
 - Bit 1 = 50%
 - Bit 2 = 25%
 - ...
 - Bit 7 (MSB) = 0.78125%
 - Average toggle rate = $(100\% + 50\% + 25\% + 12.5\% + \dots + 0.78125\%) / 8$

Enable Rate Definition

Output enable rate is the average percentage of time during which tristate outputs are enabled. When nontristate output buffers are used, the enable rate should be 100%.

Table 2-23 • Toggle Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
α_1	Toggle rate of VersaTile outputs	10%
α_2	I/O buffer toggle rate	10%

Table 2-24 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

Table 2-32 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case
Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case V_{CCI} (per standard)
Applicable to Standard Plus I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option ¹ (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{bOUT} (ns)	t_{bP} (ns)	t_{bIN} (ns)	t_{pY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTTL / 3.3 V LVCMOS	12 mA	12	High	5	—	0.97	1.75	0.18	0.85	0.66	1.79	1.40	2.36	2.79	5.38	4.99	ns
3.3 V LVCMOS Wide Range ²	100 μA	12	High	5	—	0.97	2.45	0.18	1.20	0.66	2.47	1.92	3.33	3.90	6.06	5.51	ns
2.5 V LVCMOS	12 mA	12	High	5	—	0.97	1.75	0.18	1.08	0.66	1.79	1.52	2.38	2.70	5.39	5.11	ns
1.8 V LVCMOS	8 mA	8	High	5	—	0.97	1.97	0.18	1.01	0.66	2.02	1.76	2.46	2.66	5.61	5.36	ns
1.5 V LVCMOS	4 mA	4	High	5	—	0.97	2.25	0.18	1.18	0.66	2.30	2.00	2.53	2.68	5.89	5.59	ns
3.3 V PCI	Per PCI spec	—	High	10	25 ²	0.97	1.97	0.18	0.73	0.66	2.01	1.50	2.36	2.79	5.61	5.10	ns
3.3 V PCI-X	Per PCI-X spec	—	High	10	25 ²	0.97	1.97	0.19	0.70	0.66	2.01	1.50	2.36	2.79	5.61	5.10	ns

Notes:

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.
3. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.
4. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Detailed I/O DC Characteristics

Table 2-37 • Input Capacitance

Symbol	Definition	Conditions	Min.	Max.	Units
C _{IN}	Input capacitance	V _{IN} = 0, f = 1.0 MHz		8	pF
C _{INCLK}	Input capacitance on the clock pin	V _{IN} = 0, f = 1.0 MHz		8	pF

Table 2-38 • I/O Output Buffer Maximum Resistances¹
Applicable to Advanced I/O Banks

Standard	Drive Strength	R _{PULL-DOWN} (Ω) ²	R _{PULL-UP} (Ω) ³
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	17	50
	24 mA	11	33
3.3 V LVCMOS Wide Range	100 μA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
	16 mA	20	40
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
	6 mA	67	75
	8 mA	33	37
	12 mA	33	37
1.2 V LVCMOS ⁴	2 mA	158	164
1.2 V LVCMOS Wide Range ⁴	100 μA	Same as regular 1.2 V LVCMOS	Same as regular 1.2 V LVCMOS
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / I_{OL_{spec}}$
3. $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / I_{OH_{spec}}$
4. Applicable to IGLOO V2 Devices operating at VCCI ≥ VCC

Table 2-69 • 3.3 V LVC MOS Wide Range Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: $T_j = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$
Applicable to Standard Plus Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	2 mA	Std.	0.97	5.84	0.18	1.20	0.66	5.86	5.04	2.74	2.71	9.46	8.64	ns
100 μA	4 mA	Std.	0.97	5.84	0.18	1.20	0.66	5.86	5.04	2.74	2.71	9.46	8.64	ns
100 μA	6 mA	Std.	0.97	4.76	0.18	1.20	0.66	4.78	4.33	3.09	3.33	8.37	7.93	ns
100 μA	8 mA	Std.	0.97	4.76	0.18	1.20	0.66	4.78	4.33	3.09	3.33	8.37	7.93	ns
100 μA	12 mA	Std.	0.97	4.02	0.18	1.20	0.66	4.04	3.78	3.33	3.73	7.64	7.37	ns
100 μA	16 mA	Std.	0.97	4.02	0.18	1.20	0.66	4.04	3.78	3.33	3.73	7.64	7.37	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-70 • 3.3 V LVC MOS Wide Range High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: $T_j = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.7\text{ V}$
Applicable to Standard Plus Banks

Drive Strength	Equivalent Software Default Drive Strength Option ¹	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 μA	2 mA	Std.	0.97	3.33	0.18	1.20	0.66	3.35	2.68	2.73	2.88	6.94	6.27	ns
100 μA	4 mA	Std.	0.97	3.33	0.18	1.20	0.66	3.35	2.68	2.73	2.88	6.94	6.27	ns
100 μA	6 mA	Std.	0.97	2.75	0.18	1.20	0.66	2.77	2.17	3.08	3.50	6.36	5.77	ns
100 μA	8 mA	Std.	0.97	2.75	0.18	1.20	0.66	2.77	2.17	3.08	3.50	6.36	5.77	ns
100 μA	12 mA	Std.	0.97	2.45	0.18	1.20	0.66	2.47	1.92	3.33	3.90	6.06	5.51	ns
100 μA	16 mA	Std.	0.97	2.45	0.18	1.20	0.66	2.47	1.92	3.33	3.90	6.06	5.51	ns

Notes:

1. The minimum drive strength for any LVC MOS 3.3 V software configuration when run in wide range is $\pm 100\text{ }\mu\text{A}$. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.
3. Software default selection highlighted in gray.

1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

Table 2-95 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	2	2	9	11	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	4	4	17	22	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	6	6	35	44	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	8	8	45	51	10	10
12 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	12	12	91	74	10	10
16 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	16	16	91	74	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-96 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	2	2	9	11	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	4	4	17	22	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	6	6	35	44	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	8	8	35	44	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-111 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	6	6	32	39	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	8	8	66	55	10	10
12 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	12	12	66	55	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-112 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer. Furthermore, all LVCMOS 1.2 V software macros comply with LVCMOS 1.2 V wide range as specified in the JESD8-12A specification.

Table 2-127 • Minimum and Maximum DC Input and Output Levels
Applicable to Advanced I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-128 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-129 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

1.2 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
1 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1	20	26	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at 100°C junction temperature and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Input Register

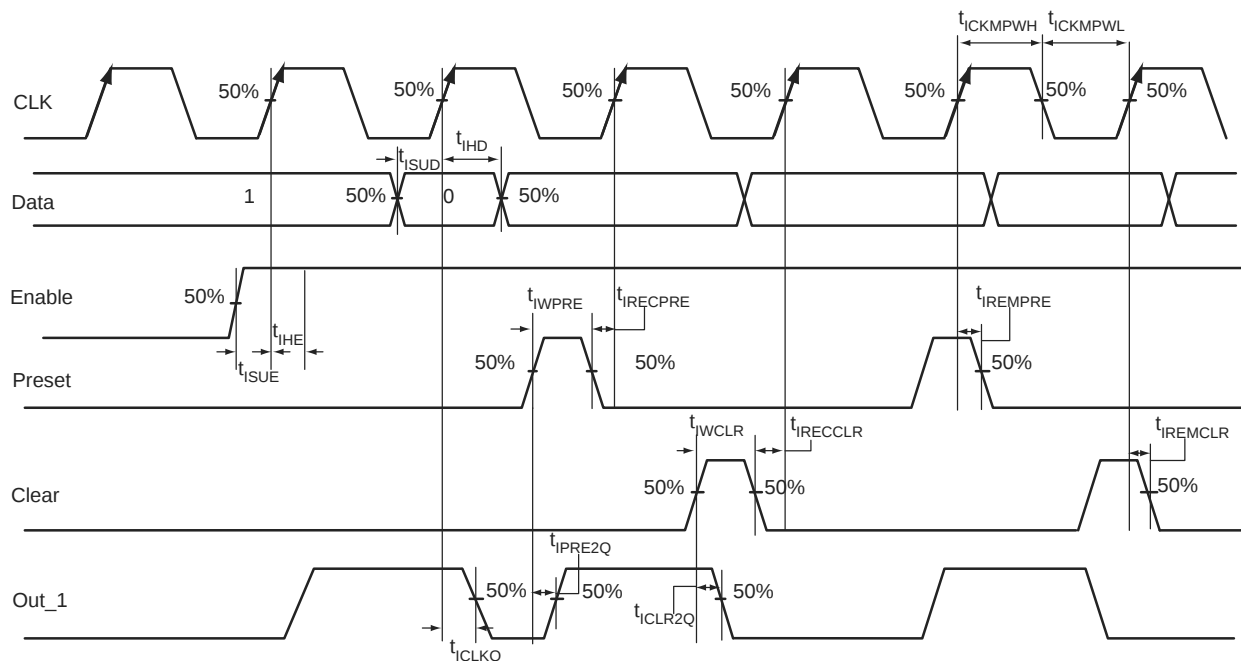


Figure 2-18 • Input Register Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-157 • Input Data Register Propagation Delays

Commercial-Case Conditions: $T_j = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.42	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.47	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	0.67	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	0.79	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	0.79	ns
t_{IEMCLR}	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
t_{IRECCLR}	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
t_{IEMPRE}	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
t_{IRECPRE}	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
t_{ICKMPWH}	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
t_{ICKMPWL}	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage**Table 2-168 • Output DDR Propagation Delays****Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	1.60	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	1.09	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	1.16	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	1.99	ns
$t_{\text{DDROREMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{\text{DDRORECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.24	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.31	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	160.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

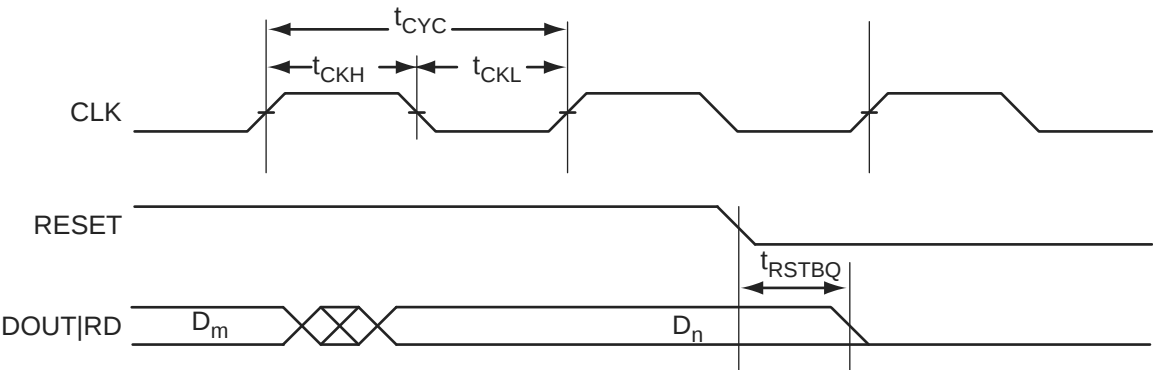


Figure 2-36 • RAM Reset. Applicable to Both RAM4K9 and RAM512x18.

FG144	
Pin Number	AGL125 Function
K1	GEB0/IO109RSB1
K2	GEA1/IO108RSB1
K3	GEA0/IO107RSB1
K4	GEA2/IO106RSB1
K5	IO100RSB1
K6	IO98RSB1
K7	GND
K8	IO73RSB1
K9	GDC2/IO72RSB1
K10	GND
K11	GDA0/IO66RSB0
K12	GDB0/IO64RSB0
L1	GND
L2	VMV1
L3	FF/GEB2/IO105RSB1
L4	IO102RSB1
L5	VCCIB1
L6	IO95RSB1
L7	IO85RSB1
L8	IO74RSB1
L9	TMS
L10	VJTAG
L11	VMV1
L12	TRST
M1	GNDQ
M2	GEC2/IO104RSB1
M3	IO103RSB1
M4	IO101RSB1
M5	IO97RSB1
M6	IO94RSB1
M7	IO86RSB1
M8	IO75RSB1
M9	TDI
M10	VCCIB1
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	AGL250 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO16RSB0
A6	GND
A7	IO29RSB0
A8	VCC
A9	IO33RSB0
A10	GBA0/IO39RSB0
A11	GBA1/IO40RSB0
A12	GNDQ
B1	GAB2/IO117UDB3
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO14RSB0
B6	IO19RSB0
B7	IO22RSB0
B8	IO30RSB0
B9	GBB0/IO37RSB0
B10	GBB1/IO38RSB0
B11	GND
B12	VMV1
C1	IO117VDB3
C2	GFA2/IO107PPB3
C3	GAC2/IO116UDB3
C4	VCC
C5	IO12RSB0
C6	IO17RSB0
C7	IO24RSB0
C8	IO31RSB0
C9	IO34RSB0
C10	GBA2/IO41PDB1
C11	IO41NDB1
C12	GBC2/IO43PPB1

FG144	
Pin Number	AGL250 Function
D1	IO112NDB3
D2	IO112PDB3
D3	IO116VDB3
D4	GAA2/IO118UPB3
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO35RSB0
D8	GBC1/IO36RSB0
D9	GBB2/IO42PDB1
D10	IO42NDB1
D11	IO43NPB1
D12	GCB1/IO49PPB1
E1	VCC
E2	GFC0/IO110NDB3
E3	GFC1/IO110PDB3
E4	VCCIB3
E5	IO118VPB3
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO48PDB1
E9	VCCIB1
E10	VCC
E11	GCA0/IO50NDB1
E12	IO51NDB1
F1	GFB0/IO109NPB3
F2	VCOMPLF
F3	GFB1/IO109PPB3
F4	IO107NPB3
F5	GND
F6	GND
F7	GND
F8	GCC0/IO48NDB1
F9	GCB0/IO49NPB1
F10	GND
F11	GCA1/IO50PDB1
F12	GCA2/IO51PDB1

FG144	
Pin Number	AGL250 Function
G1	GFA1/IO108PPB3
G2	GND
G3	VCCPLF
G4	GFA0/IO108NPB3
G5	GND
G6	GND
G7	GND
G8	GDC1/IO58UPB1
G9	IO53NDB1
G10	GCC2/IO53PDB1
G11	IO52NDB1
G12	GCB2/IO52PDB1
H1	VCC
H2	GFB2/IO106PDB3
H3	GFC2/IO105PSB3
H4	GEC1/IO100PDB3
H5	VCC
H6	IO79RSB2
H7	IO65RSB2
H8	GDB2/IO62RSB2
H9	GDC0/IO58VPB1
H10	VCCIB1
H11	IO54PSB1
H12	VCC
J1	GEB1/IO99PDB3
J2	IO106NDB3
J3	VCCIB3
J4	GEC0/IO100NDB3
J5	IO88RSB2
J6	IO81RSB2
J7	VCC
J8	TCK
J9	GDA2/IO61RSB2
J10	TDO
J11	GDA1/IO60UDB1
J12	GDB1/IO59UDB1

FG256	
Pin Number	AGL1000 Function
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	FF/GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

FG484	
Pin Number	AGL600 Function
A1	GND
A2	GND
A3	VCCIB0
A4	NC
A5	NC
A6	IO09RSB0
A7	IO15RSB0
A8	NC
A9	NC
A10	IO22RSB0
A11	IO23RSB0
A12	IO29RSB0
A13	IO35RSB0
A14	NC
A15	NC
A16	IO46RSB0
A17	IO48RSB0
A18	NC
A19	NC
A20	VCCIB0
A21	GND
A22	GND
AA1	GND
AA2	VCCIB3
AA3	NC
AA4	NC
AA5	NC
AA6	IO135RSB2
AA7	IO133RSB2
AA8	NC
AA9	NC
AA10	NC
AA11	NC
AA12	NC
AA13	NC
AA14	NC

FG484	
Pin Number	AGL600 Function
AA15	NC
AA16	IO101RSB2
AA17	NC
AA18	NC
AA19	NC
AA20	NC
AA21	VCCIB1
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB2
AB4	NC
AB5	NC
AB6	IO130RSB2
AB7	IO128RSB2
AB8	IO122RSB2
AB9	IO116RSB2
AB10	NC
AB11	NC
AB12	IO113RSB2
AB13	IO112RSB2
AB14	NC
AB15	NC
AB16	IO100RSB2
AB17	IO95RSB2
AB18	NC
AB19	NC
AB20	VCCIB2
AB21	GND
AB22	GND
B1	GND
B2	VCCIB3
B3	NC
B4	NC
B5	NC
B6	IO08RSB0

FG484	
Pin Number	AGL600 Function
B7	IO12RSB0
B8	NC
B9	NC
B10	IO17RSB0
B11	NC
B12	NC
B13	IO36RSB0
B14	NC
B15	NC
B16	IO47RSB0
B17	IO49RSB0
B18	NC
B19	NC
B20	NC
B21	VCCIB1
B22	GND
C1	VCCIB3
C2	NC
C3	NC
C4	NC
C5	GND
C6	NC
C7	NC
C8	VCC
C9	VCC
C10	NC
C11	NC
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484	
Pin Number	AGL600 Function
U1	IO149PDB3
U2	IO149NDB3
U3	NC
U4	GEB1/IO145PDB3
U5	GEB0/IO145NDB3
U6	VMV2
U7	IO138RSB2
U8	IO136RSB2
U9	IO131RSB2
U10	IO124RSB2
U11	IO119RSB2
U12	IO107RSB2
U13	IO104RSB2
U14	IO97RSB2
U15	VMV1
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO88NDB1
U20	NC
U21	IO83NDB1
U22	NC
V1	NC
V2	NC
V3	GND
V4	GEA1/IO144PDB3
V5	GEA0/IO144NDB3
V6	IO139RSB2
V7	GEC2/IO141RSB2
V8	IO132RSB2
V9	IO127RSB2
V10	IO121RSB2
V11	IO114RSB2
V12	IO109RSB2
V13	IO105RSB2
V14	IO98RSB2